

PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5108

Ka-Band 3-Stage Self Bias Low Noise Amplifier

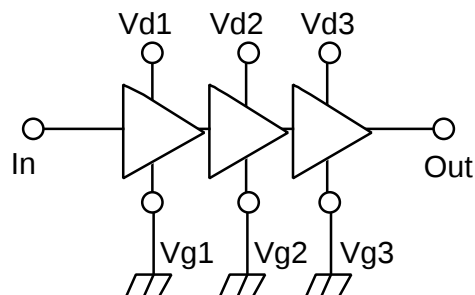
DESCRIPTION

The MGFC5108 is a GaAs MMIC chip especially designed for 24.0 ~ 27.0 GHz band Low Noise Amplifier.(LNA) .

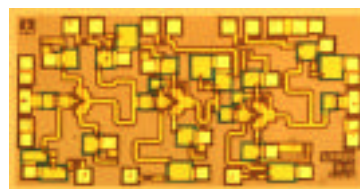
FEATURES

- RF frequency : 24.0 to 27.0 GHz
- Super Low Noise NF=2.5dB (TYP.)
- Single voltage operation

BLOCK DIAGRAM



PHOTOGRAPH



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	5	V
Id	Drain bias current	30	mA
Vg	Gate bias voltage	-	V
Pin	Maximum peak input power overdrive (Duration < 1sec)	TBD	dBm
Ta	Operating temperature range	TBD	°C

TARGET SPECIFICATIONS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
Fop	Operating frequency range	On-wafer measurement	24.0		27.0	GHz
Gain	Small signal gain		17.0	18.0		dB
Delta gain	Small signal gain flatness			1.5		dB
NF	Noise figure			2.5		dB
VSWR in	Input VSWR				2.5:1	
VSWR out	Output VSWR				2.5:1	
P1dB	Output power at 1 dB compression	Freq=22GHz Vd=5V,Id=30mA		(5) TBD		dBm
Output IP3	Output power at 3rd-order intercept point			(17) TBD		dBm
Vd	Drain bias voltage			5		V
Id	Drain bias current			30		mA
Vg	Gate bias voltage			No need		V



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as of July '98

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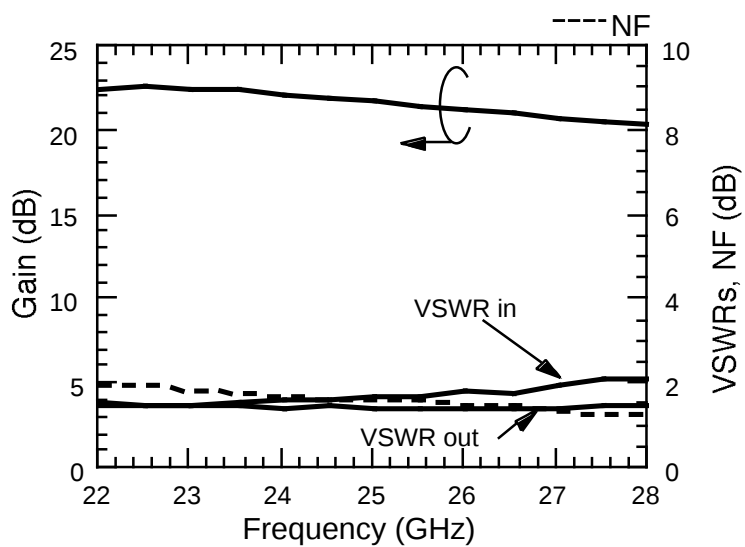
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TYPICAL CHARACTERISTICS

Small Signal Performances

($V_d = 5.0$ V, $I_d = 30$ mA, $T_a = 25$ °C)



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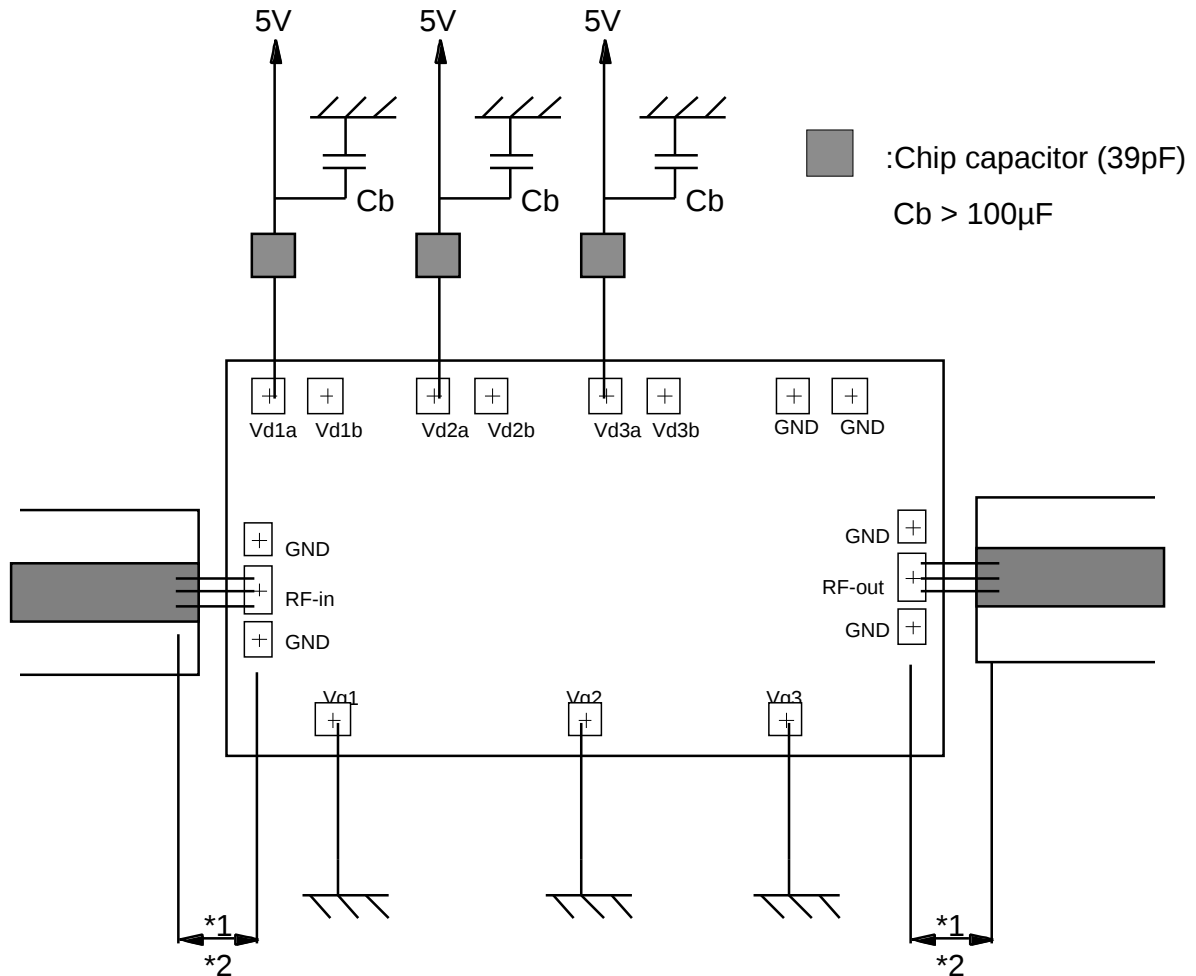
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AN EXAMPLE OF TEST CIRCUIT



*1 Length of bonding wire < 200 μm

*2 Number of bonding wire ≥ 3

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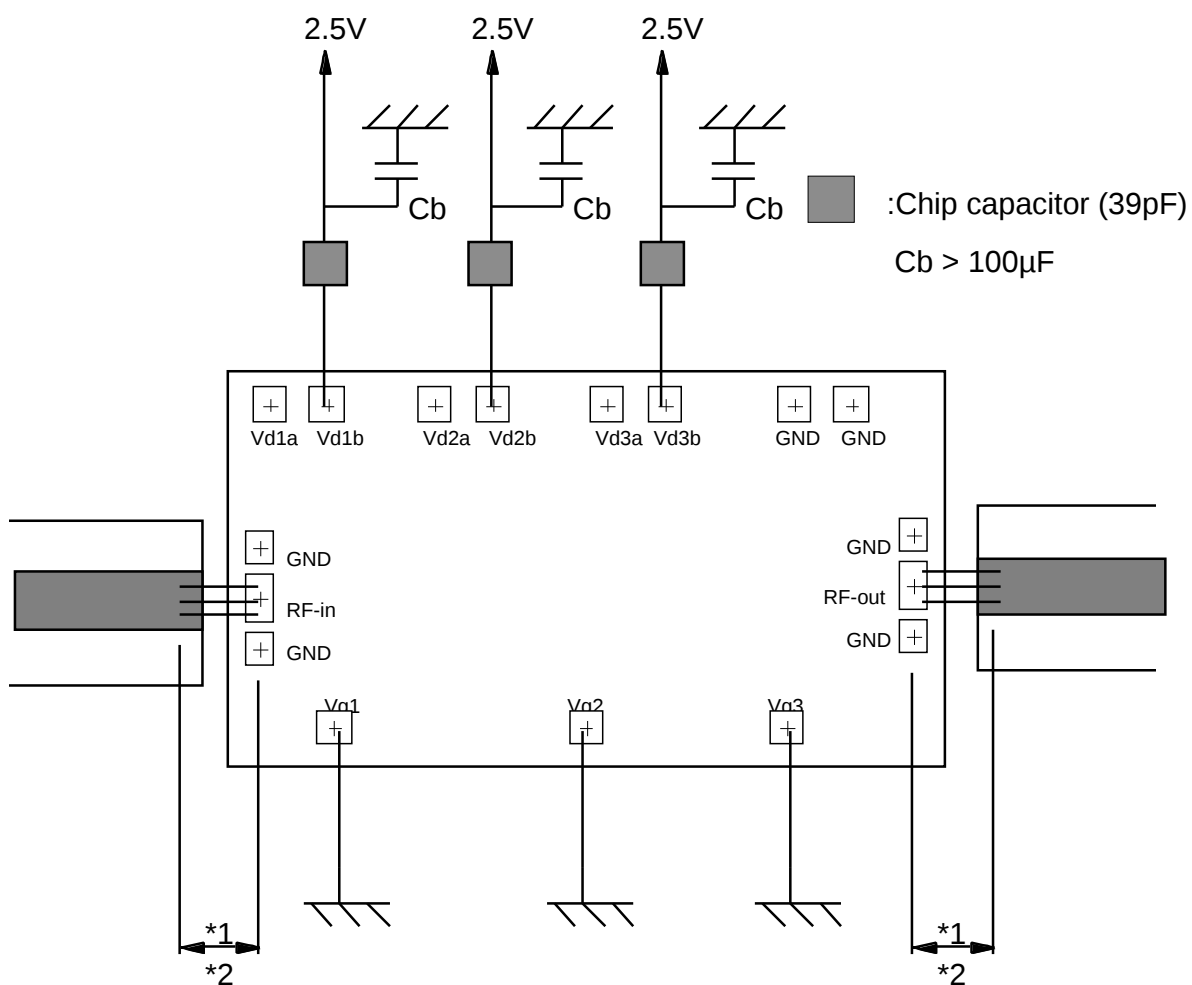
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